

Schottky Barrier Rectifier

RoHS
Compliant

Features

- Metal of silicon rectifier, majority carrier conduction
- Trench schottky technology
- Low forward voltage drop, high efficiency
- High current capability
- High surge capacity
- Plastic package has UL flammability classification 94V-0
- For use in low voltage, high frequency inverters, free wheeling, switching power supplies, DC-DC converter, and polarity protection applications



Mechanical Data

Case	: JEDEC DO-15 molded plastic
Polarity	: Colour band denotes cathode
Weight	: 0.04ounces, 1.1 grams
Mounting position	: Any

Maximum Ratings And Electrical Characteristics

Rating at 25°C ambient temperature unless otherwise specified.
Single phase, half wave, 60Hz, resistive or inductive load.
For capacitive load, derate current by 20%

Characteristic	Symbol	Values	Unit		
Maximum Ratings (T_A = 25 °C unless otherwise noted)					
Maximum Recurrent Peak Reverse Voltage	V _{RRM}	100	V		
Maximum RMS Voltage	V _{RMS}	70			
Maximum DC Blocking Voltage	V _{DC}	100			
Maximum Average Forward Rectified Current	I(AV)	5	A		
Peak Forward Surge Current 8.3ms Single Half Sine-Wave Super Imposed on Rated Load	I _{FSM}	35			
Peak repetitive reverse current at t _p = 2μs, 1kHz	I _{RRM}	2			
Operating Temperature Range	T _J	-55 to +150	°C		
Storage Temperature Range	T _{STG}	-55 to +175			
Electrical Characteristics (T_A = 25 °C unless otherwise noted)					
Parameter / Conditions	Symbol	Typ	Max	Unit	
Breakdown voltage per diode	V _{BR}	105 (minimum)	-	V	
Forward Voltage (Note1)	V _F	I _F =2.5A @T _J =25°C	0.56		0.6
		I _F =2.5A @T _J =125°C	0.52		0.56
		I _F =5A @T _J =25°C	0.7		0.75
		I _F =5A @T _J =125°C	0.64		0.68
Maximum DC Reverse Current at Rated DC Bolcking Voltage	I _R	20 20		μA mA	
Typical Junction Capacitance (Note 2)	C _J	217		pF	

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Thermal Characteristics (T _A = 25 °C unless otherwise noted)			
Parameter	Symbol	Values	Unit
Thermal Resistance Per Diode (Note3)	R _{θJL}	8	°C/W
Thermal Resistance Per Diode (Note4)	R _{θJC}		

Notes:

1. 300µs pulse width, 2% duty cycle.
2. Measured at 1MHz and applied reverse voltage of 4V DC.
3. Thermal resistance junction to lead.
4. Thermal resistance junction to case.

Rating and Characteristic Curves

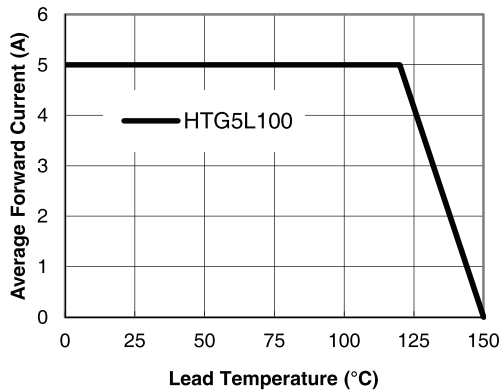


Figure 1. Forward Current Derating Curve

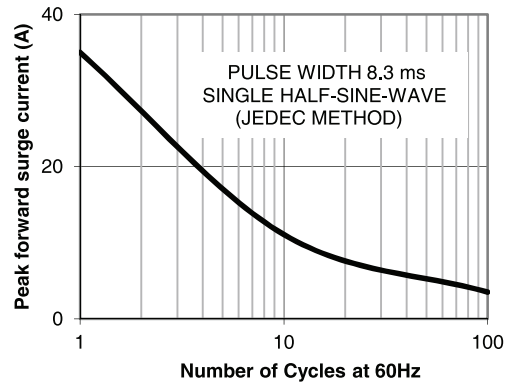


Figure 2. Maximum NON-Repetitive

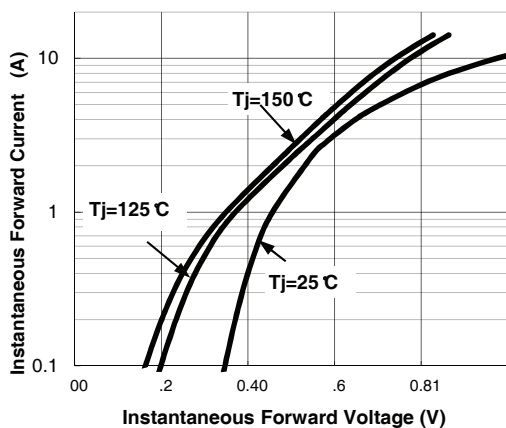


Figure 3. Typical Instantaneous Forward Characteristics Per Leg

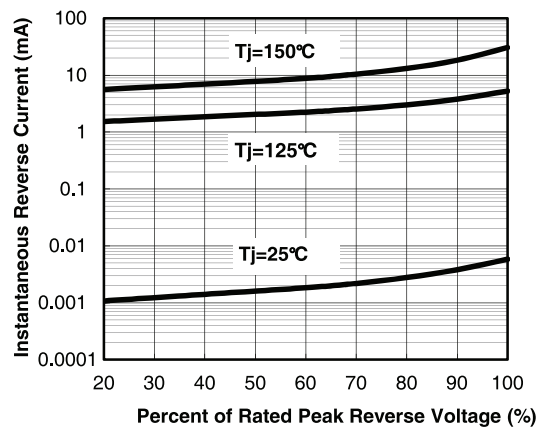


Figure 4. Typical Reverse Characteristics

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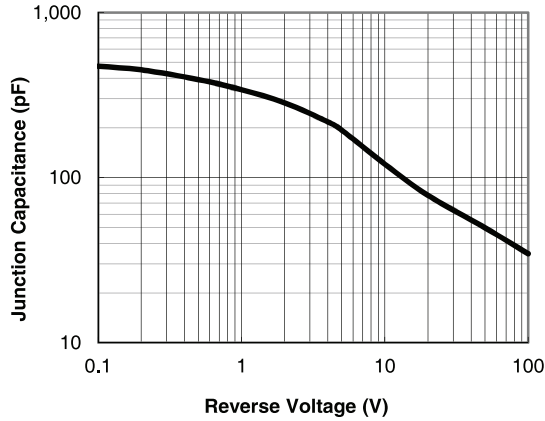


Figure 5. Typical Junction Capacitance

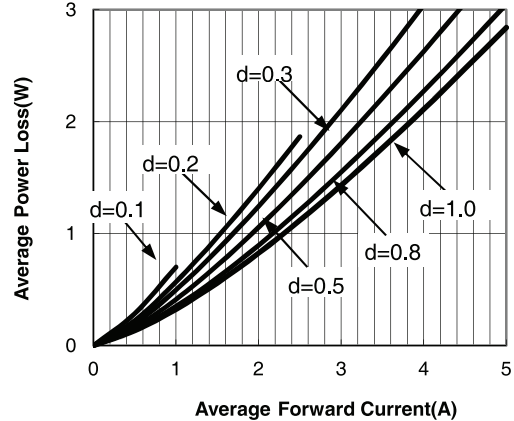
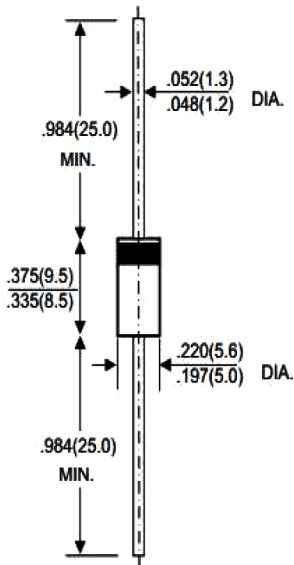


Figure 6. Forward Power Loss Characteristics

Dimension:

DO-27



Dimensions : Inches (Millimetres)

Part Number Table

Description	Part Number
Schottky Barrier Rectifier	HTG5L100

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